



# BAP50-02

General purpose PIN diode

Rev. 02 — 3 January 2008

Product data sheet

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NXP Semiconductors

# General purpose PIN diode

# BAP50-02

### FEATURES

- Low diode capacitance
- Low diode forward resistance.

### APPLICATIONS

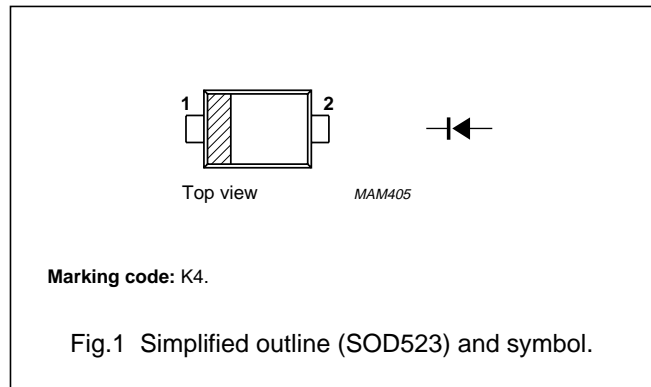
- General RF applications.

### DESCRIPTION

General purpose PIN diode in a SOD523 small SMD plastic package.

### PINNING

PIN	DESCRIPTION
1	cathode
2	anode



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		–	50	V
$I_F$	continuous forward current		–	50	mA
$P_{tot}$	total power dissipation	$T_s = 90\text{ °C}$	–	715	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–65	+150	°C

## General purpose PIN diode

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**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	forward voltage	$I_F = 50\text{ mA}$	–	0.95	1.1	V
$V_R$	reverse voltage	$I_R = 10\text{ }\mu\text{A}$	50	–	–	V
$I_R$	reverse current	$V_R = 50\text{ V}$	–	–	100	nA
$C_d$	diode capacitance	$V_R = 0; f = 1\text{ MHz}$	–	0.4	–	pF
		$V_R = 1\text{ V}; f = 1\text{ MHz}$	–	0.3	0.55	pF
		$V_R = 5\text{ V}; f = 1\text{ MHz}$	–	0.22	0.35	pF
$r_D$	diode forward resistance	$I_F = 0.5\text{ mA}; f = 100\text{ MHz}; \text{note 1}$	–	25	40	$\Omega$
		$I_F = 1\text{ mA}; f = 100\text{ MHz}; \text{note 1}$	–	14	25	$\Omega$
		$I_F = 10\text{ mA}; f = 100\text{ MHz}; \text{note 1}$	–	3	5	$\Omega$
$ S_{21} ^2$	isolation	$V_R = 0; f = 900\text{ MHz}$	–	20.4	–	dB
		$V_R = 0; f = 1800\text{ MHz}$	–	17.3	–	dB
		$V_R = 0; f = 2450\text{ MHz}$	–	15.5	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 0.5\text{ mA}; f = 900\text{ MHz}$	–	1.74	–	dB
		$I_F = 0.5\text{ mA}; f = 1800\text{ MHz}$	–	1.79	–	dB
		$I_F = 0.5\text{ mA}; f = 2450\text{ MHz}$	–	1.88	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 1\text{ mA}; f = 900\text{ MHz}$	–	1.03	–	dB
		$I_F = 1\text{ mA}; f = 1800\text{ MHz}$	–	1.09	–	dB
		$I_F = 1\text{ mA}; f = 2450\text{ MHz}$	–	1.15	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 10\text{ mA}; f = 900\text{ MHz}$	–	0.26	–	dB
		$I_F = 10\text{ mA}; f = 1800\text{ MHz}$	–	0.32	–	dB
		$I_F = 10\text{ mA}; f = 2450\text{ MHz}$	–	0.34	–	dB
$\tau_L$	charge carrier life time	when switched from $I_F = 10\text{ mA}$ to $I_R = 6\text{ mA}; R_L = 100\text{ }\Omega$ ; measured at $I_R = 3\text{ mA}$	–	1.05	–	$\mu\text{s}$
$L_S$	series inductance	$I_F = 100\text{ mA}; f = 100\text{ MHz}$	–	0.6	–	nH

**Note**

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

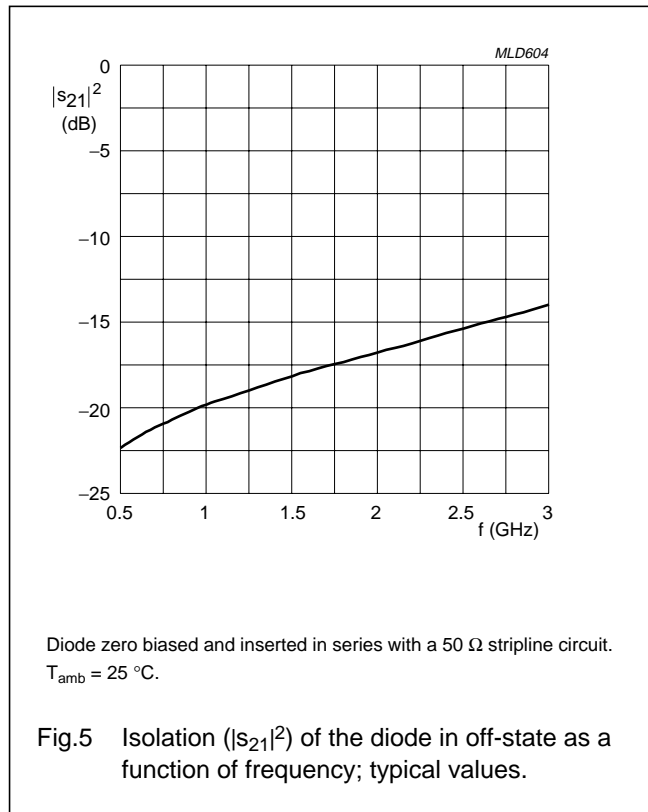
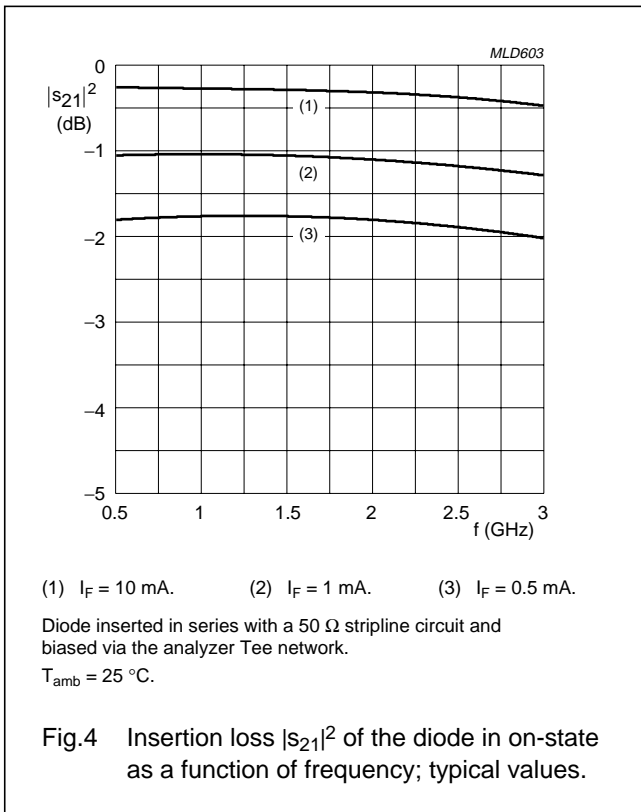
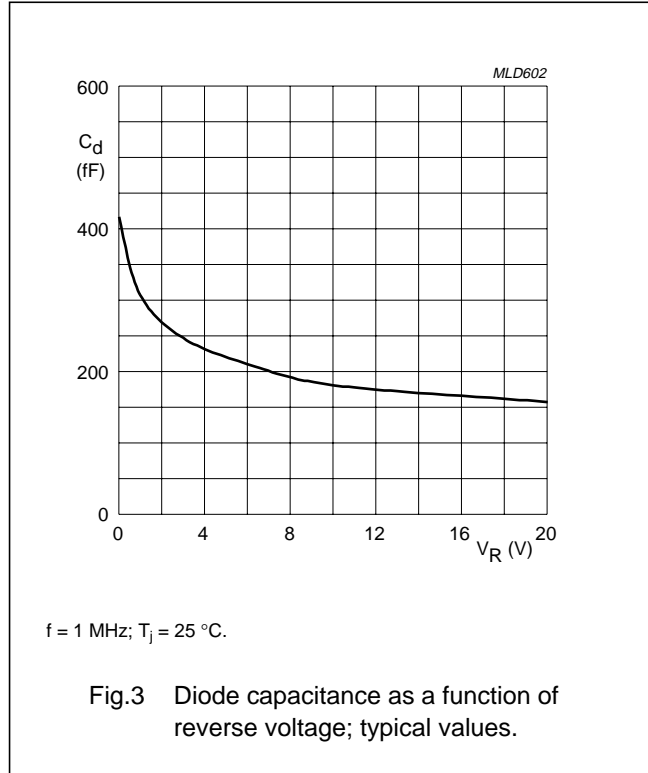
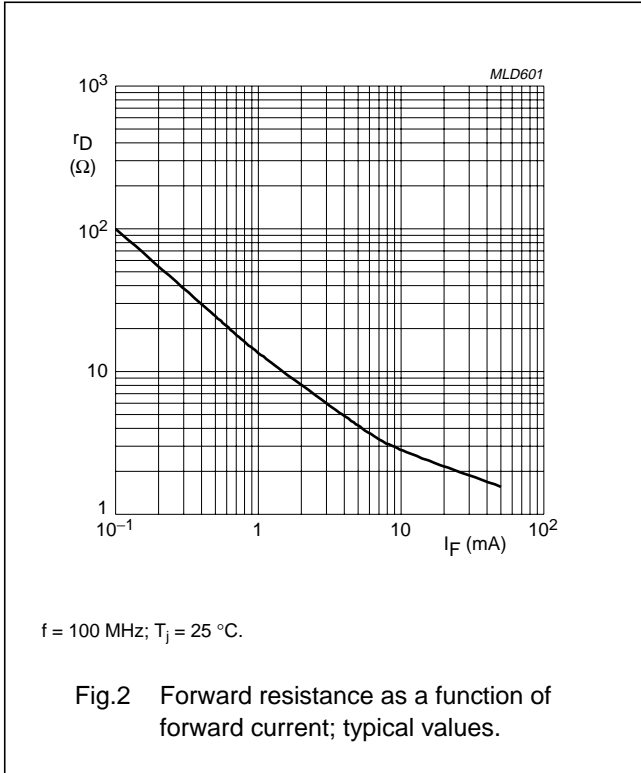
**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	85	K/W

General purpose PIN diode

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GRAPHICAL DATA



General purpose PIN diode

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PACKAGE OUTLINE

Plastic surface-mounted package; 2 leads

SOD523

**DIMENSIONS (mm are the original dimensions)**

UNIT	A	bp	c	D	E	HE	v
mm	0.65	0.34	0.17	1.25	0.85	1.65	0.1
	0.58	0.26	0.11	1.15	0.75	1.55	

**Note**  
1. The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD523			SC-79			02-12-13-06-03-16

## Legal information

### Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## Revision history

### Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP50-02_N_2	20080103	Product data sheet	-	BAP50-02_1
Modifications:	• Package outline drawing on page 5 changed			
BAP50-02_1 (9397 750 08113)	20010417	Product specification	-	-

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